

N-Channel 150 V (D-S) MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	150				
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.0315				
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5 \text{ V}$	0.037				
Q _g typ. (nC)	7.7				
I _D (A) ^a	26.2				
Configuration	Single				

FEATURES

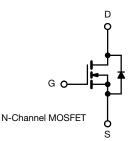
- TrenchFET® Gen V power MOSFET
- Very low R_{DS} x Q_g figure of merit (FOM)
- Tuned for the lowest R_{DS} x Q_{oss} FOM
- 100 % R_a and UIS tested

 Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



APPLICATIONS

- Synchronous rectification
- · Primary side switch
- DC/DC converters
- · OR-ing and hot swap switch
- Power supplies
- · Motor drive control
- Battery management



ORDERING INFORMATION	
Package	PowerPAK 1212-8S
Lead (Pb)-free and halogen-free	SISS5710DN-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	150		
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current (T _J = 150 °C)	T _C = 25 °C		26.2		
	T _C = 70 °C	1 ,	21.0		
	T _A = 25 °C	I _D	7.2 ^{b, c}		
	T _A = 70 °C		5.8 ^{b, c}	Α	
Pulsed drain current (t = 100 μs)		I _{DM}	70		
Octobra de la desta de la constitución de la consti	T _C = 25 °C		49.4		
Continuous source-drain diode current	T _A = 25 °C	I _S	3.7 ^{b, c}		
Single pulse avalanche current L = 0.1 mH		I _{AS}	15		
Single pulse avalanche energy		E _{AS}	11.25	mJ	
	T _C = 25 °C		54.3		
Maritim and a superior designation of the contract of the cont	T _C = 70 °C		34.7	14/	
Maximum power dissipation	T _A = 25 °C	P _D	4.1 b, c	W	
	T _A = 70 °C		2.6 ^{b, c}		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature) d, e			260		

THERMAL RESISTANCE RATING	S				
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^b	t ≤ 10 s	R _{thJA}	23	30	°C/W
Maximum junction-to-case (drain)	Steady state	R _{thJC}	1.9	2.3	0/ ٧٧

Notes

- a. $T_C = 25 \,^{\circ}C$
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 10 :
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8S is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 75 °C/W



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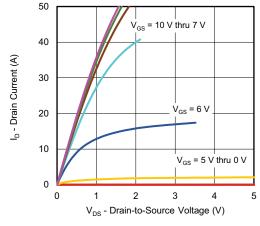
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static			•			
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 1 mA	150	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	I _D = 10 mA	-	106	-	>//00
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-7.7	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zana anta calta an dunin accument		V _{DS} = 120 V, V _{GS} = 0 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 120 V, V _{GS} = 0 V, T _J = 70 °C	-	-	15	μA
Davis and a state and a state and a	-	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	0.026	0.0315	
Drain-source on-state resistance a	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, I_D = 10 \text{ A}$	-	0.0305	0.037	Ω
Forward transconductance a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	19	-	S
Dynamic ^b			1			I.
Input capacitance	C _{iss}		-	770	-	pF
Output capacitance	C _{oss}	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	105	-	
Reverse transfer capacitance	C _{rss}		-	6.8	-	
Table de de co		$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	10	15	
Total gate charge	Q _g		-	7.7	12	
Gate-source charge	Q _{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 7.5 \text{ V}, I_D = 10 \text{ A}$	-	5.0	-	nC
Gate-drain charge	Q _{gd}		-	1.15	-	
Output charge	Q _{oss}	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}$	-	33	-	
Gate resistance	R_g	f = 1 MHz	0.5	1.4	2.4	Ω
Turn-on delay time	t _{d(on)}		-	11	22	
Rise time	t _r	$V_{DD} = 75 \text{ V. R}_1 = 7.5 \Omega$	-	7	14	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	12	24	
Fall time	t _f	f = 1 MHz V_{DD} = 75 V, R_L = 7.5 $Ω$		13	26	
Turn-on delay time	t _{d(on)}		-	12	24	ns
Rise time	t _r	$V_{DD} = 75 \text{ V}, R_1 = 7.5 \Omega$	-	8	16	- -
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 7.5 \text{ V}, R_g = 1 \Omega$	-	11	22	
Fall time	t _f		-	13	26	
Drain-Source Body Diode Characteristic	s		1			I.
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	49.4	_
Pulse diode forward current ($t_p = 100 \mu s$)	I _{SM}		-	-	70	А
Body diode voltage	V _{SD}	I _S = 5 A	-	0.81	1.1	V
Body diode reverse recovery time	t _{rr}		-	75	150	ns
Body diode reverse recovery charge	Q _{rr}	I _E = 10 A, di/dt = 100 A/us.	-	113	225	nC
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$		-	55	-		
Reverse recovery rise time	t _b		-	20	-	ns

Notes

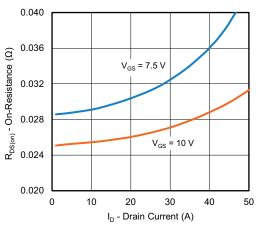
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

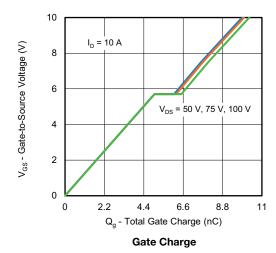


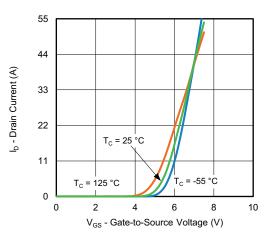


Output Characteristics

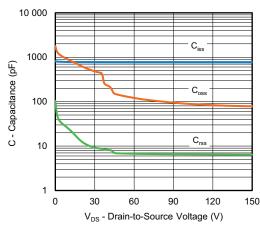


On-Resistance vs. Drain Current

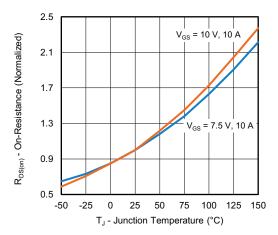




Transfer Characteristics

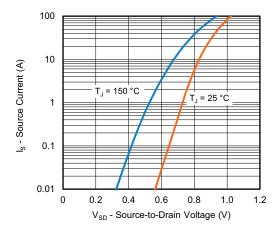


Capacitance

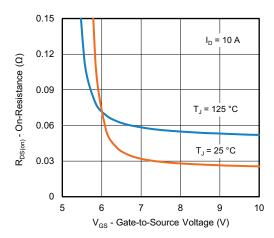


On-Resistance vs. Junction Temperature

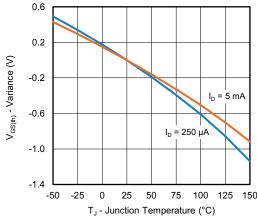




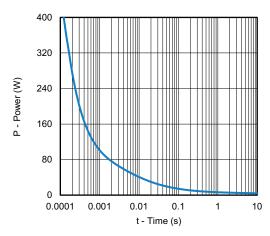
Source-Drain Diode Forward Voltage



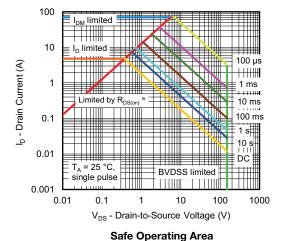
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



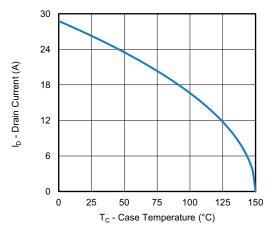
Single Pulse Power, Junction-to-Ambient



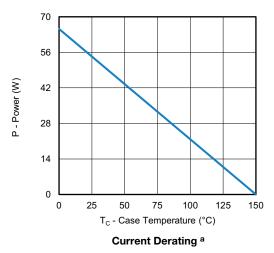
Note

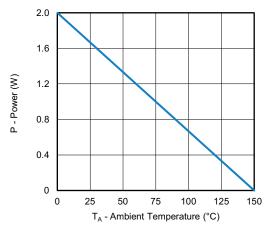
a. $V_{GS} > minimum V_{GS}$ at which $R_{DS(on)}$ is specified





Power, Junction-to-Case



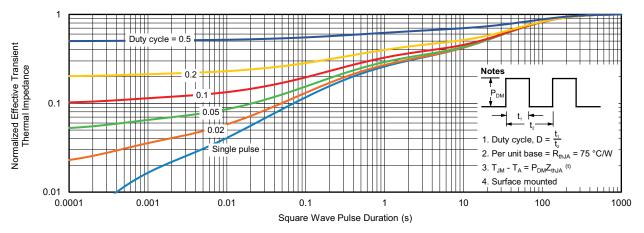


Power, Junction-to-Ambient

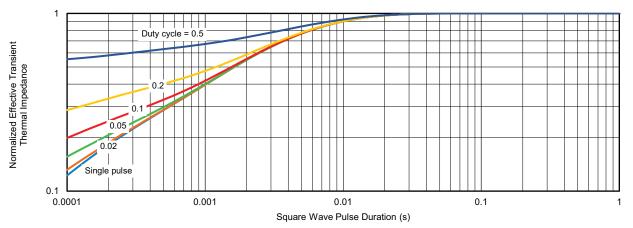
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

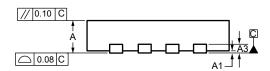
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Case Outline for PowerPAK® 1212-8S





DIM.	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN. NOM.		MAX.	
Α	0.67	0.75	0.83	0.026	0.030	0.033	
A1	0.00	-	0.05	0.000	-	0.002	
A3		0.20 ref.			0.008 ref		
b	0.25	0.30	0.35	0.010	0.012	0.014	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.15	2.25	2.35	0.085	0.089	0.093	
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	1.60	1.70	1.80	0.063	0.067	0.071	
е		0.65 bsc.			0.026 bsc.		
K		0.76 ref.			0.030 ref.		
K1	0.41 ref.			0.41 ref. 0.016 ref.			
L	0.33	0.43	0.53	0.013	0.017	0.021	
Z	0.525 ref.				0.021 ref.		

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DWG: 6008



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